II B. Tech I Semester Regular/Supplementary Examinations, October/November - 2018 BASIC ELECTRONICS AND DEVICES

Tir	ne: 3	3 hours Max	x. Marks: 70
		Note: 1. Question Paper consists of two parts (Part-A and Part-B) 2. Answer ALL the question in Part-A 3. Answer any FOUR Questions from Part-B	
		<u>PART -A</u>	
1.	a)	Define hole and explain how they move in semiconductor.	(3M)
	b)	What is meant by tunneling?	(2M)
	c)	Draw the circuit diagram of L-section filter and write the expression for ripple factor.	e (3M)
	d)	What are the different configurations of BJT?	(2M)
	e)	Why a field effect transistor is called so?	(2M)
	f)	Give the comparison of power amplifiers in terms of operating cycle and efficiency.	d (2M)
		PART -B	
2.	a)	Explain the diffusion concept in semiconductors with necessary equations.	(7M)
	b)	Explain the concept of Generation and Recombination of charges.	(7M)
3.	a)	Explain the following terms: (i) Static Resistance (ii) Dynamic Resistance (iii) cut-in voltage	(7M)
	b)	Explain the operation of Light Emitting Diode and write its applications.	(7M)
4.	a)	What is regulation? Derive the expression for regulation for half-wave rectifier and full-wave rectifier.	r (7M)
	b)	A full wave rectifier delivers 50 W to a load of 200 Ω . If the ripple factor is 1%, calculate ac ripple voltage across the load.	(7M)
5.	a)	What is early effect? What are the consequences of it in BJT? Explain.	(7M)
	b)	Draw the circuit diagram of self bias circuit and derive the expression for stability factor S.	r (7M)
6.	a)	Explain the construction of N channel JFET and explain its operation.	(7M)
	b)	Explain the operation of power IGBT.	(7M)
7.	a)	Draw the circuit diagram of RC phase shift oscillator and explain its operation.	(7M)
	b)	A voltage series negative feedback amplifier has a voltage gain withou feedback of A = 500, input resistance R_i = 3 k Ω , output resistance R_0 = 20 k Ω and feedback ratio β = 0.01. Calculate the voltage gain A_f , input resistance R_{if} and output resistance R_{of} of the amplifier with feedback.	2

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Tiı	me: 3	S hours Max.	Marks: 7
		Note: 1. Question Paper consists of two parts (Part-A and Part-B) 2. Answer ALL the question in Part-A 3. Answer any FOUR Questions from Part-B	
		<u>PART -A</u>	
1.	a)	Write the difference between intrinsic and extrinsic semiconductors.	(2M)
	b)	What is PIN diode?	(2M)
	c)	Compare various rectifiers in terms of ripple factor.	(2M)
	d)	Define α and β . Write the relationship between them.	(3M)
	e)	Write the application of FET.	(2M)
	f)	What are the advantages of negative feedback?	(3M)
		PART -B	
2.	a)	What is meant by an energy band? Explain the classification materials based on	(7M)
	b)	energy band. Explain the concept of Injected minority carrier charge with necessary equations.	(7M)
3.	a)	Discuss about current components in p-n junction diode.	(7M)
	b)	With the help of energy band diagrams, explain the operation of tunnel diode.	(7M)
4.	a)	Draw the circuit diagram of rectifier with capacitor filter and explain how it reduces the ripples in the output.	(7M)
	b)	The turns ratio of the transformer used in a half wave rectifier is 2:1 and the primary is connected to 230 V, 50 Hz power mains. Assuming the diode is to be ideal, determine (i) dc voltage across the load (ii) PIV (iii) dc power delivered to the load having a resistance of 200 Ω .	(7M)
5.	a)	Explain the input and output characteristics of NPN transistor in CC	(7M)
	b)	configuration. Determine the voltage gain, current gain, input impedance and output impedance of a CE amplifier using NPN transistor with h_{ie} = 1200 $\Omega,\ h_{re}$ = 0, h_{fe} = 36, h_{oe} = 2 x 10 $^{-6}$ mhos, R_L = 2.5 k $\Omega,\ R_S$ = 500 $\Omega.$	(7M)
6.	a)	Explain the V-I characteristics of silicon controlled rectifier.	(7M)
	b)	Draw the low frequency model of FET and explain it.	(7M)
7.	a)	Explain the basic principles behind push-pull amplifiers.	(7M)
	b)	Draw the circuit diagram of Wien bridge oscillator circuit and explain its operation.	(7M)

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Time: 3 hou	(Electrical and Electronics Engineering) rs M	ax. Marks: 70
	Note: 1. Question Paper consists of two parts (Part-A and Part-B) 2. Answer ALL the question in Part-A 3. Answer any FOUR Questions from Part-B	
	<u>PART -A</u>	
1. a) Stat	e and explain mass action law.	(3M)
b) Wh	at is photo diode? Write its applications.	(2M)
c) Def	ine ripple factor and write its significance.	(2M)
d) Wh	at are the drawbacks of fixed bias circuit?	(2M)
e) Wh	at are the advantages of MOSFET when compared to JFET?	(2M)
f) Wri	te short notes on total harmonic distortion.	(3M)
	<u>PART -B</u>	
2. a) Wh	at is meant by doping? How it improves the conductivity? Explain.	(7M)
writ	tch the Fermi level in both intrinsic and extrinsic semiconductors. At the expressions for Fermi level in both intrinsic and extrinsic semiconductors.	, ,
3. a) Wh	at is meant by diffusion capacitance? Derive the expression for it.	(7M)
	plain in detail about avalanche breakdown and zener breakdown. Explaeffect of temperature on these two breakdown mechanisms.	ain (7M)
	w the circuit diagram of Bridge rectifier and explain its operation. Write tantages of it.	the (7M)
b) An tran resi	ac supply of 230 V is applied to a half-wave rectifier circuit throus sformer of turns ratio 5: 1. Assume the diode is an ideal one. The lostance is 300 Ω . Find (i) dc output voltage (ii) PIV (iii) average value load current.	oad
5. a) _{Exp}	plain how the transistor is used as an amplifier and switch.	(7M)
b) Dra	w the hybrid model of transistor in CE, CB and CC configuration. List of advantages of transistor hybrid parameters.	out (7M)
	plain the construction details of depletion MOSFET and its trans	fer (7M)
	mpare various power semiconductor devices.	(7M)
7. a) _{Exp}	plain the concept of feedback and write the advantages of negative feedback	ck. (7M)
b) Dra	w the block diagram of an oscillator and explain it.	(7M)

SET - 4 Code No: R1621023 **R16**

II B. Tech I Semester Regular/Supplementary Examinations, October/November - 2018 BASIC ELECTRONICS AND DEVICES

(Electrical and Electronics Engineering) Time: 3 hours Max			
		Note: 1. Question Paper consists of two parts (Part-A and Part-B) 2. Answer ALL the question in Part-A 3. Answer any FOUR Questions from Part-B	
		<u>PART –A</u>	
1.	a)	Write the Einstein relationship in semiconductors.	(2M)
	b)	Draw the symbols of tunnel diode, Zener diode, photo diode and LED.	(2M)
	c)	Define efficiency of a rectifier.	(2M)
	d)	What is meant by transistor biasing?	(2M)
	e)	List out the applications of SCR.	(3M)
	f)	Give the classification of power amplifiers.	(3M)
		PART -B	
2.	a)	List out the properties of semiconductor and explain how these properties	(7M)
	b)	changes with respect to temperature. What is law of junction? Derive the expression for it.	(7M)
3.	a)	Explain the operation of p-n diode in both forward and reverse bias conditions.	(7M)
	b)	Explain the operation of Varactor diode and write its applications.	(7M)
4.	a)	Draw the circuit diagram of Zener diode regulator and explain its operation.	(7M)
	b)	In a bridge rectifier, the transformer is connected to 200 V, 60 Hz mains and the turn's ratio of the step down transformer is 11:1. Assuming the diode is ideal and load is 600Ω , find (i) I_{dc} (ii) voltage across the load (iii) PIV	(7M)
5.	a)	Describe the all current components in bipolar junction transistor.	(7M)
		Draw the collector to base bias circuit and explain it.	(7M)
6.			(7M)
0.	a)	Explain the volt-ampere characteristics of enhancement MOSFET.	
	b)	Explain how the FET acts as an amplifier.	(7M)
7.	a)	List out the different types of negative feedback configurations and draw their block diagrams.	(7M)
	b)	Explain about crystal oscillator.	(7M)